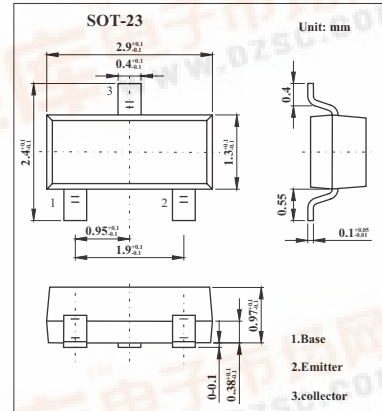


SMD Type Transistors

Silicon NPN Triple Diffused Type  
2SC4497

Features

- High voltage.
- Low saturation voltage.
- Small collector output capacitance.



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	300	V
Collector-emitter voltage	V <sub>CEO</sub>	300	V
Emitter-base voltage	V <sub>EB0</sub>	6	V
Collector current	I <sub>c</sub>	100	mA
Base current	I <sub>B</sub>	20	mA
Collector power dissipation	P <sub>C</sub>	200	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = 300 V, I <sub>E</sub> = 0			0.1	μA
Emitter cut-off current	I <sub>EB0</sub>	V <sub>EB</sub> = 6 V, I <sub>c</sub> = 0			0.1	μA
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>c</sub> = 0.1 mA, I <sub>E</sub> = 0	300			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>c</sub> = 1 mA, I <sub>B</sub> = 0	300			V
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 10 V, I <sub>c</sub> = 20 mA	30		150	
		V <sub>CE</sub> = 10 V, I <sub>c</sub> = 1 mA	20			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> = 20 mA, I <sub>B</sub> = 2 mA			0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> = 20 mA, I <sub>B</sub> = 2 mA			1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 10 V, I <sub>c</sub> = 10 mA		70		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 20 V, I <sub>E</sub> = 0, f = 1 MHz		3	4	pF

hFE Classification

Marking	3R	3O
Rank	R	O
hFE	30~90	50~150

